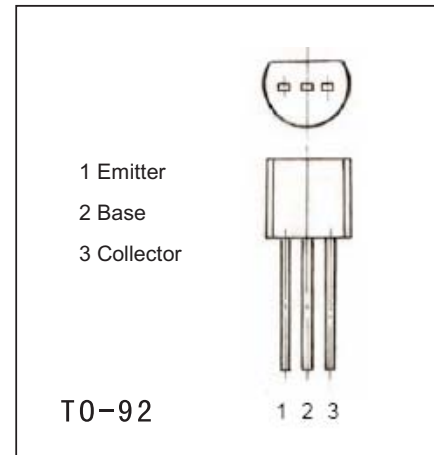


■ Features

- High voltage



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	400	V
Collector-Emitter Voltage	V _{CEO}	400	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current -Continuous	I _c	0.2	A
Collector Power Dissipation	P _c	0.625	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to 150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CB0}	I _c =100uA, I _E =0	400			V
Collector-emitter breakdown voltage	V _{CEO}	I _c =1mA, I _B =0	400			V
Emitter-base Breakdown voltage	V _{EB0}	I _E =100 μ A, I _c =0	5			V
Collector cutoff current	I _{cBO}	V _{CB} =400V, I _E =0			0.1	μA
Collector cutoff current	I _{CEO}	V _{CB} =400V, I _B =0			5	μ A
Emitter cutoff current	I _{EB0}	V _{EB} =4V, I _c =0			0.1	μA
DC current gain	h _{FE}	V _{CE} =10V, I _c =10mA	80		300	
		V _{CE} =10V, I _c =1mA	70			
		V _{CE} =10V, I _c =100mA	40			
		V _{CE} =10V, I _c =50mA	80			
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =10mA, I _B =1mA			0.2	V
		I _c =50mA, I _B =5mA			0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _c =10mA, I _B =1mA			0.75	V
Transition frequency	f _r	V _{CE} =20V, I _c =10mA, f=30MHZ	50			MHz